

Joon Sue Lee

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

38
papers

2,637
citations

19
h-index

40
g-index

40
ext. papers

3,171
ext. citations

9.7
avg, IF

4.69
L-index

#	Paper	IF	Citations
38	Supercurrent parity meter in a nanowire Cooper pair transistor.. <i>Science Advances</i> , 2022 , 8, eabm9896	14.3	0
37	Parity-preserving and magnetic field-resilient superconductivity in InSb nanowires with Sn shells. <i>Science</i> , 2021 , 372, 508-511	33.3	13
36	Topological materials by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2020 , 128, 210902	2.5	12
35	Evaluation of the vortex core size in gate-tunable Josephson junctions in Corbino geometry. <i>Physical Review B</i> , 2020 , 102,	3.3	1
34	Transport studies in a gate-tunable three-terminal Josephson junction. <i>Physical Review B</i> , 2020 , 101,	3.3	13
33	Conductance-Matrix Symmetries of a Three-Terminal Hybrid Device. <i>Physical Review Letters</i> , 2020 , 124, 036802	7.4	22
32	In-plane selective area InSb/Al nanowire quantum networks. <i>Communications Physics</i> , 2020 , 3,	5.4	18
31	Large-scale interlayer rotations and Te grain boundaries in (Bi,Sb) ₂ Te ₃ thin films. <i>Physical Review Materials</i> , 2020 , 4,	3.2	8
30	Adsorption-controlled growth of MnTe(Bi ₂ Te ₃) _n by molecular beam epitaxy exhibiting stoichiometry-controlled magnetism. <i>Physical Review Materials</i> , 2020 , 4,	3.2	7
29	Strong electron-electron interactions of a Tomonaga-Luttinger liquid observed in InAs quantum wires. <i>Physical Review B</i> , 2019 , 99,	3.3	9
28	Transport Studies of Epi-Al/InAs Two-Dimensional Electron Gas Systems for Required Building-Blocks in Topological Superconductor Networks. <i>Nano Letters</i> , 2019 , 19, 3083-3090	11.5	15
27	On the understanding of current-induced spin polarization of three-dimensional topological insulators. <i>Nature Communications</i> , 2019 , 10, 1461	17.4	7
26	Contribution of top barrier materials to high mobility in near-surface InAs quantum wells grown on GaSb(001). <i>Physical Review Materials</i> , 2019 , 3,	3.2	8
25	Structure and basal twinning of topological insulator Bi ₂ Se ₃ grown by MBE onto crystalline Y ₃ Fe ₅ O ₁₂ . <i>Physical Review Materials</i> , 2019 , 3,	3.2	7
24	Selective-area chemical beam epitaxy of in-plane InAs one-dimensional channels grown on InP(001), InP(111)B, and InP(011) surfaces. <i>Physical Review Materials</i> , 2019 , 3,	3.2	26
23	End-to-end correlated subgap states in hybrid nanowires. <i>Physical Review B</i> , 2019 , 100,	3.3	20
22	Unidirectional spin-Hall and Rashba-Edelstein magnetoresistance in topological insulator-ferromagnet layer heterostructures. <i>Nature Communications</i> , 2018 , 9, 111	17.4	55

21	Quantized Majorana conductance. <i>Nature</i> , 2018 , 556, 74-79	50.4	382
20	Materials considerations for forming the topological insulator phase in InAs/GaSb heterostructures. <i>Physical Review Materials</i> , 2018 , 2,	3.2	14
19	Electric field tunable superconductor-semiconductor coupling in Majorana nanowires. <i>New Journal of Physics</i> , 2018 , 20, 103049	2.9	44
18	Mirage Andreev Spectra Generated by Mesoscopic Leads in Nanowire Quantum Dots. <i>Physical Review Letters</i> , 2018 , 121, 127705	7.4	15
17	Engineering the breaking of time-reversal symmetry in gate-tunable hybrid ferromagnet/topological insulator heterostructures. <i>Npj Quantum Materials</i> , 2018 , 3,	5	17
16	Faraday Rotation Due to Surface States in the Topological Insulator (BiSb)Te. <i>Nano Letters</i> , 2017 , 17, 980-984	11.5	19
15	Epitaxy of advanced nanowire quantum devices. <i>Nature</i> , 2017 , 548, 434-438	50.4	192
14	Probing Two-dimensional (Bi,Sb) ₂ Te ₃ /h-BN Heterostructures Using Complementary S/TEM and Simulation Techniques. <i>Microscopy and Microanalysis</i> , 2017 , 23, 1760-1761	0.5	
13	S/TEM Investigation of the Structure of (Bi,Sb) ₂ Te ₃ /h-BN Heterostructures Grown by Molecular Beam Epitaxy. <i>Microscopy and Microanalysis</i> , 2016 , 22, 1602-1603	0.5	
12	Surface-State-Dominated Spin-Charge Current Conversion in Topological-Insulator-Ferromagnetic-Insulator Heterostructures. <i>Physical Review Letters</i> , 2016 , 117, 076601	7.4	130
11	Giant Spin Pumping and Inverse Spin Hall Effect in the Presence of Surface and Bulk Spin-Orbit Coupling of Topological Insulator Bi ₂ Se ₃ . <i>Nano Letters</i> , 2015 , 15, 7126-32	11.5	200
10	Characterizing the structure of topological insulator thin films. <i>APL Materials</i> , 2015 , 3, 083303	5.7	40
9	Sum-rule constraints on the surface state conductance of topological insulators. <i>Physical Review Letters</i> , 2015 , 115, 116804	7.4	20
8	Mapping the chemical potential dependence of current-induced spin polarization in a topological insulator. <i>Physical Review B</i> , 2015 , 92,	3.3	66
7	Infrared electrodynamics and ferromagnetism in the topological semiconductors Bi ₂ Te ₃ and Mn-doped Bi ₂ Te ₃ . <i>Physical Review B</i> , 2014 , 89,	3.3	19
6	Spin-transfer torque generated by a topological insulator. <i>Nature</i> , 2014 , 511, 449-51	50.4	851
5	Ferromagnetism and spin-dependent transport in n-type Mn-doped bismuth telluride thin films. <i>Physical Review B</i> , 2014 , 89,	3.3	40
4	Molecular beam epitaxial growth of Bi ₂ Te ₃ and Sb ₂ Te ₃ topological insulators on GaAs (111) substrates: a potential route to fabricate topological insulator p-n junction. <i>AIP Advances</i> , 2013 , 3, 072112	12.5	56

- 3 Anomalous anisotropic magnetoresistance in topological insulator films. *Nano Research*, **2012**, 5, 739-746 59
- 2 Superconducting proximity effect and possible evidence for Pearl vortices in a candidate topological insulator. *Physical Review B*, **2011**, 84, 3-3 115
- 1 Coherent heteroepitaxy of Bi₂Se₃ on GaAs (111)B. *Applied Physics Letters*, **2010**, 97, 262104 3-4 116